

| L Number | Hits | Search Text | DB | Time stamp |
|----------|--------|---|----------------------------------|------------------|
| - | 136905 | ((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM) | USPAT; US-PGPUB | 2004/08/05 15:19 |
| - | 115095 | ((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole) | USPAT; US-PGPUB | 2004/08/05 15:20 |
| - | 14226 | (((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate) | USPAT; US-PGPUB | 2004/08/05 15:20 |
| - | 8567 | (((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate) | USPAT; US-PGPUB | 2004/08/05 15:21 |
| - | 1983 | (((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate)) and spacer | USPAT; US-PGPUB | 2004/08/05 15:21 |
| - | 1224 | (((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate)) and spacer) and ((polysilicon silicon polycide) near15 spacer) | USPAT; US-PGPUB | 2004/08/05 15:19 |
| - | 60905 | ((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM) | EPO; JPO; DERWENT; IBM_TDB | 2004/08/05 15:19 |
| - | 1268 | (((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate)) and spacer) and ((polysilicon silicon polycide) with spacer) | USPAT; US-PGPUB | 2004/08/05 15:19 |
| - | 7846 | ((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole) | EPO; JPO; DERWENT; IBM_TDB | 2004/08/05 15:20 |
| - | 1367 | (((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate) | EPO; JPO; DERWENT; IBM_TDB | 2004/08/05 15:21 |
| - | 1160 | (((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate) | EPO; JPO; DERWENT; IBM_TDB | 2004/08/05 15:21 |
| - | 148 | (((((non?volatile (non near3 volatile) volatile flash split) near8 memory) or (EEPROM EPROM PROM E2PROM)) and (trench recess open\$4 via groove hole)) and (control near3 gate)) and (float\$3 near3 gate)) and spacer | EPO; JPO; DERWENT; IBM_TDB | 2004/08/05 15:21 |